

L Number	Hits	Search Text	DB	Time stamp
-	0	("densified dielectric").PN.	USPAT; US-PGPUB; EPO; JPO	2002/07/18 16:18
-	0	("densified").PN.	USPAT; US-PGPUB; EPO; JPO	2002/07/18 17:15
-	0	("densified").PN.	USPAT	2002/07/18 17:15
-	8939	densification	USPAT	2002/07/18 17:15
-	71	densification near dielectric	USPAT	2002/07/18 17:16
-	616	densification same dielectric	USPAT	2002/07/18 17:15
-	25	(densification near dielectric) and plasma	USPAT	2002/07/18 17:22
-	697	"low k dielectric"	USPAT; US-PGPUB; EPO; JPO	2002/07/18 17:23
-	105	"low k dielectric" same "etch stop"	USPAT; US-PGPUB; EPO; JPO	2002/07/18 17:38
-	1	6054379.pn.	USPAT	2002/07/18 17:48
-	271	treat\$3 near dielectric	USPAT; US-PGPUB; EPO; JPO	2002/07/18 17:49
-	87	(treat\$3 near dielectric) and plasma	USPAT; US-PGPUB; EPO; JPO	2002/07/18 17:53
-	11	((treat\$3 near dielectric) and plasma) and "etch stop"	USPAT; US-PGPUB; EPO; JPO	2002/07/18 17:56
-	2	5314845.pn.	USPAT; US-PGPUB; EPO; JPO	2002/07/18 17:58
-	2	5915203.pn.	USPAT; US-PGPUB; EPO; JPO	2002/07/18 18:00
-	2	("6303047" "6365528").pn.	USPAT; US-PGPUB; EPO; JPO	2002/07/18 18:06
-	44591	silicon with carbide	USPAT; US-PGPUB; EPO; JPO	2002/07/18 18:06
-	42528	silicon with carbon	USPAT; US-PGPUB; EPO; JPO	2002/07/18 18:07
-	73891	(silicon with carbide) or (silicon with carbon)	USPAT; US-PGPUB; EPO; JPO	2002/07/18 18:07
-	19286	((silicon with carbide) or (silicon with carbon)) same (plasma densified plasma Hydrogen He Helium Ar Argon NH3 ammonia N2 nitrogen)	USPAT; US-PGPUB; EPO; JPO	2002/07/18 18:09
-	189	((silicon with carbide) or (silicon with carbon)) same (plasma densified plasma Hydrogen He Helium Ar Argon NH3 ammonia N2 nitrogen)) and "low k"	USPAT; US-PGPUB; EPO; JPO	2002/07/18 18:10
-	167	((silicon with carbide) or (silicon with carbon)) same (plasma densified plasma Hydrogen He Helium Ar Argon NH3 ammonia N2 nitrogen)) and "low k") and etch\$3	USPAT; US-PGPUB; EPO; JPO	2002/07/18 18:10
-	1620	"dual damascene" and etch\$3	USPAT; US-PGPUB; EPO; JPO	2002/07/19 09:40
-	110	("dual damascene" and etch\$3) and "etch mask"	USPAT; US-PGPUB; EPO; JPO	2002/07/19 09:40

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-	103	((("dual damascene" and etch\$3) and "etch mask") and (vias via trenches trench))	USPAT; US-PGPUB; EPO; JPO	2002/07/19 09:42
-	101	((("dual damascene" and etch\$3) and "etch mask") and (vias via trenches trench)) and pattern\$3	USPAT; US-PGPUB; EPO; JPO	2002/07/19 09:42
-	39	((("dual damascene" and etch\$3) and "etch mask") and (vias via trenches trench)) and pattern\$3) and "low k"	USPAT; US-PGPUB; EPO; JPO	2002/07/19 09:49
-	1511	convert\$3 near6 dielectric	USPAT; US-PGPUB; EPO; JPO	2002/07/19 09:54
-	452	(convert\$3 near6 dielectric) and etch\$	USPAT; US-PGPUB; EPO; JPO	2002/07/19 09:55
-	59	((convert\$3 near6 dielectric) and etch\$) and ("etch mask" "etch stop")	USPAT; US-PGPUB; EPO; JPO	2002/07/19 09:55
-	226	photoresist adj mask adj5 dielectric	USPAT; EPO; JPO	2003/05/14 21:25
-	0	(photoresist adj mask adj5 dielectric) and "densified dielectric"	USPAT; EPO; JPO	2003/05/14 21:24
-	221	(photoresist adj mask adj5 dielectric) and etch\$3	USPAT; EPO; JPO	2003/05/14 21:25
-	3240	etch\$3 adj3 sidewall	USPAT; EPO; JPO	2003/05/14 21:25
-	10	(photoresist adj mask adj5 dielectric) and (etch\$3 adj3 sidewall)	USPAT; EPO; JPO	2003/05/14 21:30
-	2493	"low-k" "low k"	USPAT; EPO; JPO	2003/10/09 13:48
-	1450	("low-k" "low k") with dielectric	USPAT; EPO; JPO	2003/10/09 13:49
-	712	((("low-k" "low k") with dielectric) and damascene	USPAT; EPO; JPO	2003/10/09 13:49
-	532	((("low-k" "low k") with dielectric) and damascene) and plasma	USPAT; EPO; JPO	2003/10/09 13:49
-	528	((("low-k" "low k") with dielectric) and damascene) and plasma) and etch\$3	USPAT; EPO; JPO	2003/10/09 13:49
-	10632	"etch stop" "etch mask"	USPAT; EPO; JPO	2003/10/09 13:49
-	309	("etch stop" "etch mask") and (((("low-k" "low k") with dielectric) and damascene) and plasma) and etch\$3)	USPAT; EPO; JPO	2003/10/09 14:03
-	1	6,028,015.pn.	USPAT; EPO; JPO	2003/10/09 14:04
-	1	6,028,015.pn. and photoresist	USPAT; EPO; JPO	2003/10/09 14:08
-	1	6,028,015.pn. and mask	USPAT; EPO; JPO	2003/10/09 14:09
-	1	6,028,015.pn. and pattern\$3	USPAT; EPO; JPO	2003/10/09 14:09